Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3k	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	70	mA
				80	
I_H	I_T =500mA		MAX.	50	mA
dV/dt	V_D=800V Gate Open T_j =125		MIN.	4000	V s
(dI/dt)c	j=125		MIN.	18	A/ms
t_{on}	I_G=80mA I_A=400mA I_R=40mA T_j=25		TYP.	10	s
t_{off}				70	

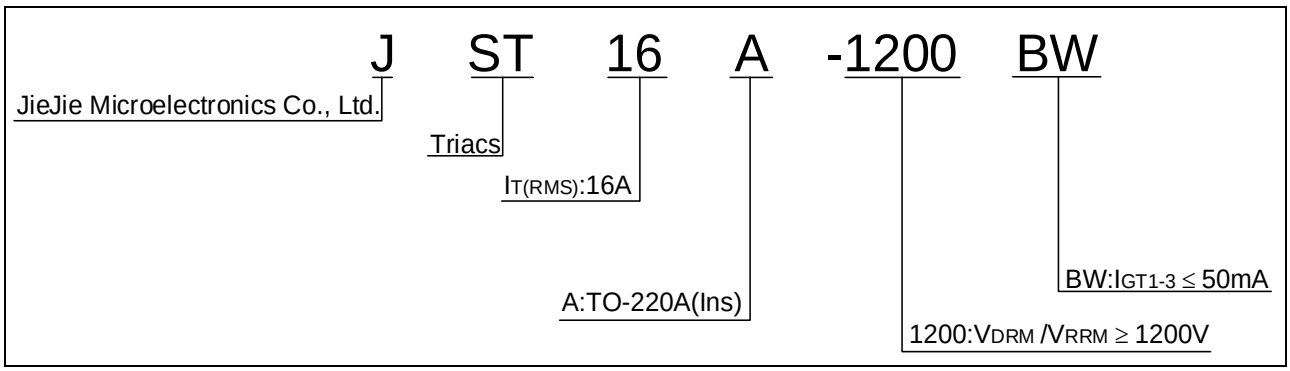
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =22.5A t_p=380 s	T_j=25	1.5	V
V_{TO}	Threshold voltage	T_j=125	0.77	V
R_D	Dynamic resistance	T_j=125	32	
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25	10	A
I_{RRM}		T_j=125	2	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

ORDERING INFORMATION



MARKING

FIG.1: Maximum power dissipation versus RMS on-state current



FIG.2: RMS on-state current versus case temperature

ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		H I- J			
JST16A-1200BW	1200	50	TO-220A(Ins)	50	Tube

Document Revision History

Date	

PACKAGE MECHANICAL DATA

